Silicon NPN Power Transistors 2SC2563

DESCRIPTION

·With TO-3P(I) package
·High power dissipation

APPLICATIONS

·For audio power amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

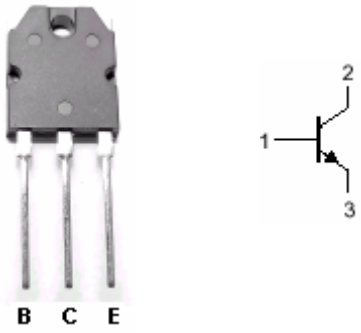

Fig.1 simplified outline (TO-3P(I)) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	120	V
V_{CEO}	Collector-emitter voltage	Open base	120	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
P_T	Total power dissipation	T_C=25□	80	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ,I_B=0	120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ,I_C=0	5			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=4A; I_B=0.4A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=120V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			50	μA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	55		160	
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=5V	35			
f_T	Transition frequency	I_C=1A ; V_{CE}=5V		90		MHz

PACKAGE OUTLINE

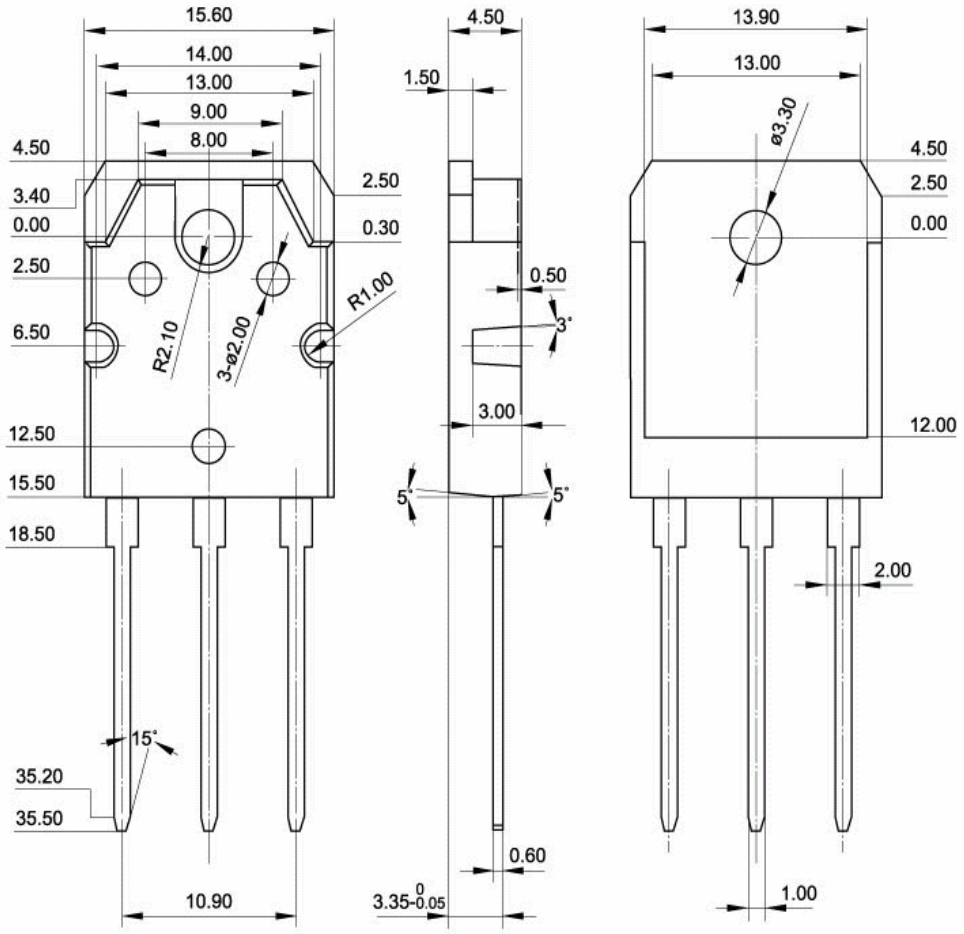

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)